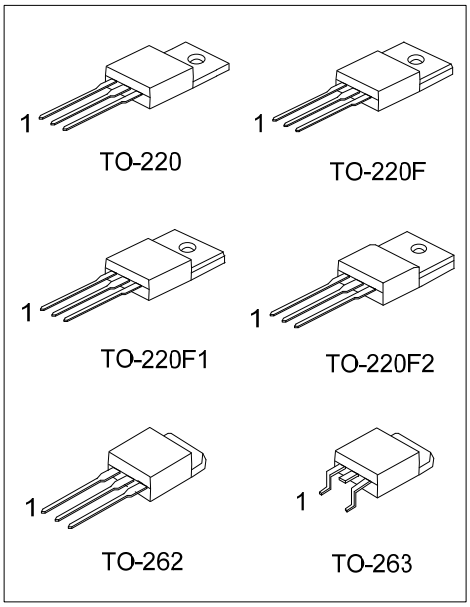
13N50

Power MOSFET

13A, 500V N-CHANNEL POWER MOSFET



■ DESCRIPTION

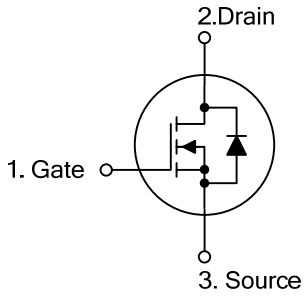
The UTC **13N50** is a N-Channel enhancement mode power MOSFET. The device adopts planar stripe and uses DMOS technology to minimize and provide lower on-state resistance and faster switching speed. It can also withstand high energy pulse under the avalanche and commutation mode conditions.

The UTC **13N50** is ideally suitable for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge topology.

■ FEATURES

* $R_{DS(ON)}$ < 0.48Ω @ V_{GS} = 10V, I_D = 6.5A
* Avalanche energy tested

■ SYMBOL



■ ORDERING INFORMATION

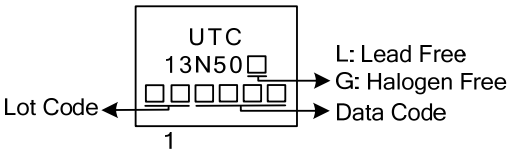
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
13N50L-TA3-T	13N50G-TA3-T	TO-220	G	D	S	Tube
13N50L-TF3-T	13N50G-TF3-T	TO-220F	G	D	S	Tube
13N50L-TF1-T	13N50G-TF1-T	TO-220F1	G	D	S	Tube
13N50L-TF2-T	13N50G-TF2-T	TO-220F2	G	D	S	Tube
13N50L-T2Q-T	13N50G-T2Q-T	TO-262	G	D	S	Tube
13N50L-TQ2-T	13N50G-TQ2-T	TO-263	G	D	S	Tube
13N50L-TQ2-R	13N50G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

13N50G-TA3-T
(1) Packing Type
(2) Package Type
(3) Green Package

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1
TF2: TO-220F2, T2Q: TO-262, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	13	A
	Pulsed (Note 2)	I_{DM}	52	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	972	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.1	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P_D	168	W
	TO-220F/TO-220F1 TO-220F2		35	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=11.5mH, I_{AS}=13A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD}≤13A, di/dt≤200A/μs, V_{DD}≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

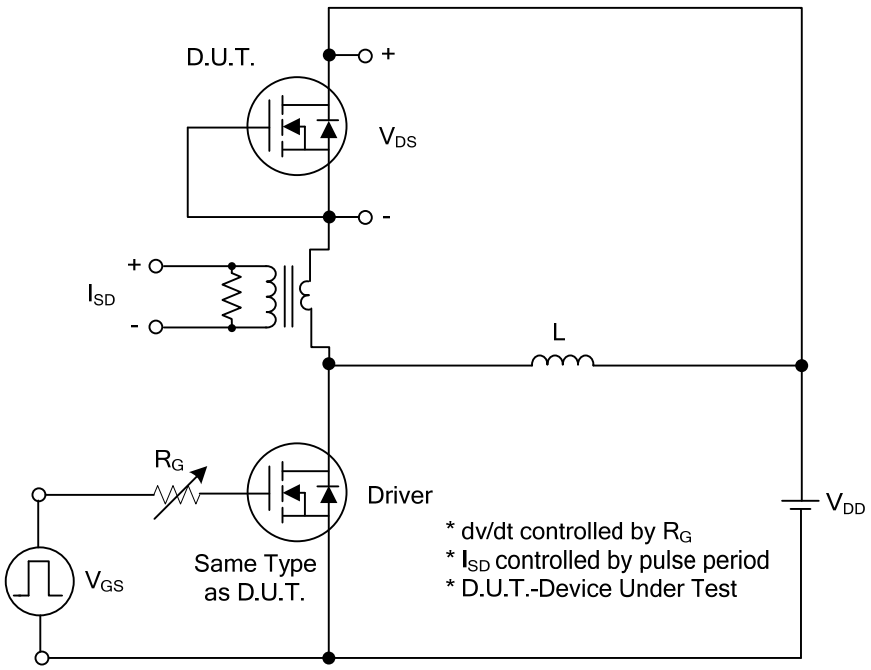
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220/TO-262 TO-263	θ_{JC}	0.74	°C/W
	TO-220F/TO-220F1 TO-220F2		3.57	

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

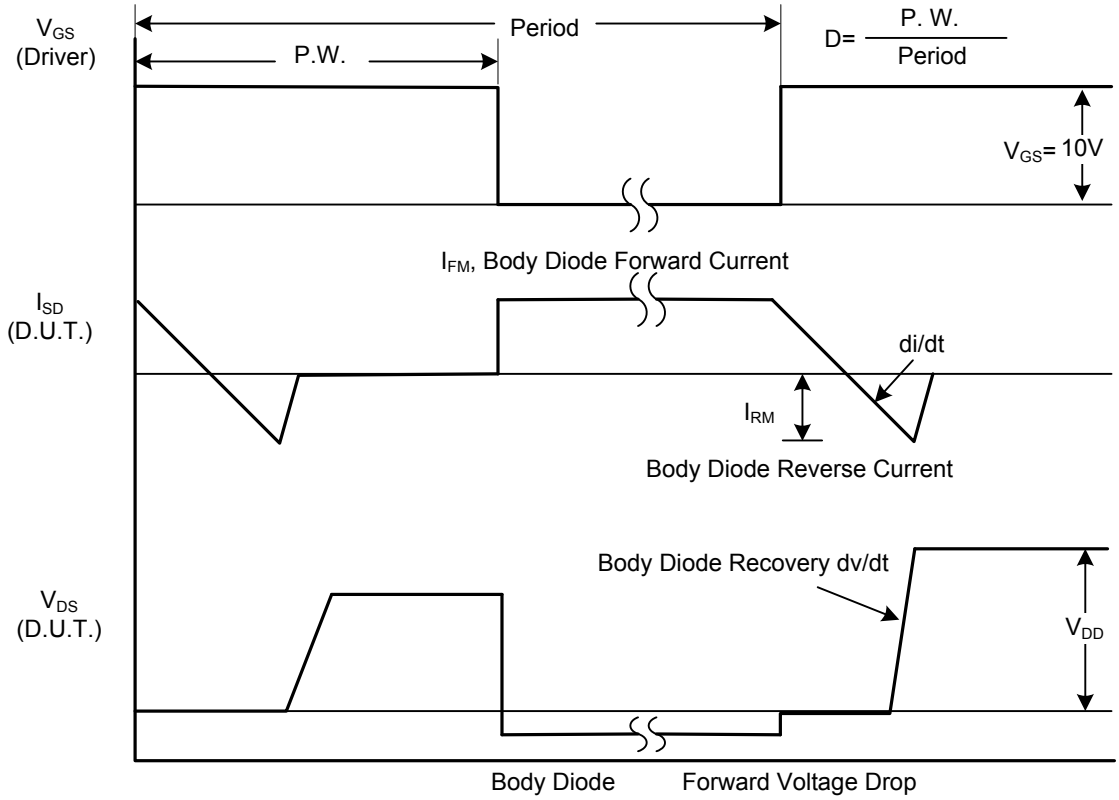
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA	500			V
Drain-Source Leakage Current	I_{DSS}	V_{DS} = 500V, V_{GS} = 0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
		V_{GS} = -30V, V_{DS} = 0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 6.5A			0.48	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1920		pF
Output Capacitance	C_{OSS}			235		pF
Reverse Transfer Capacitance	C_{RSS}			36		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=400V, V_{GS}=10V, I_D=13A, I_D=1mA (Note 1, 2)		60		nC
Gate to Source Charge	Q_{GS}			16		nC
Gate to Drain Charge	Q_{GD}			24		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DS}=250V, V_{GS}=10V, I_D=13A, R_G=25Ω (Note 1, 2)		27		nS
Rise Time	t_R			25		nS
Turn-OFF Delay Time	$t_{D(OFF)}$			140		nS
Fall-Time	t_F			35		nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				13	A
Maximum Body-Diode Pulsed Current	I_{SM}				52	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S=13A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	I_S=13A, V_{GS}=0V, dI_F/dt=100A/μs		380		nS
Body Diode Reverse Recovery Charge	Q_{rr}			5.5		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

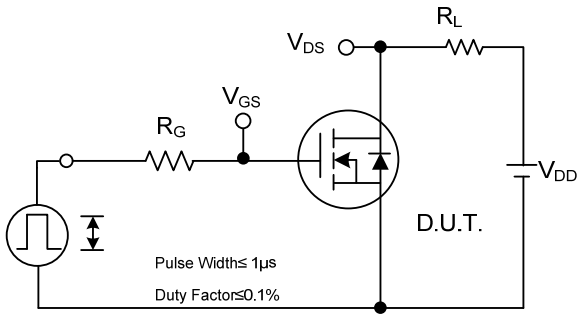


Peak Diode Recovery dv/dt Test Circuit

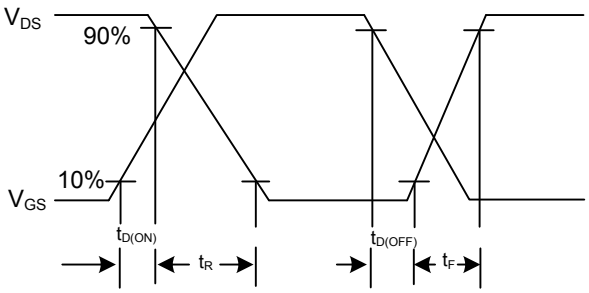


Peak Diode Recovery dv/dt Waveforms

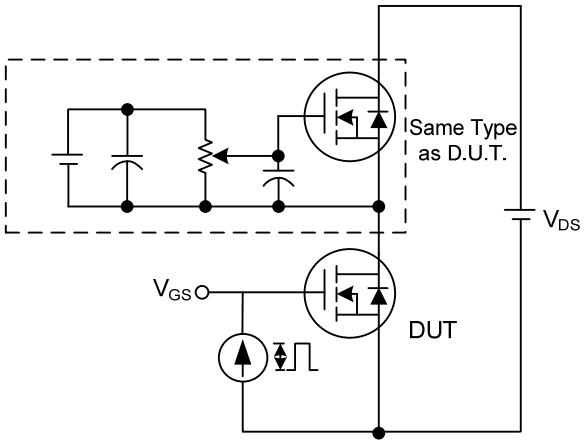
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



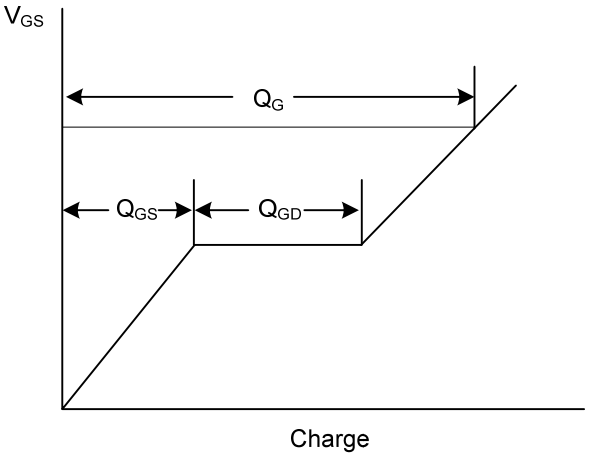
Switching Test Circuit



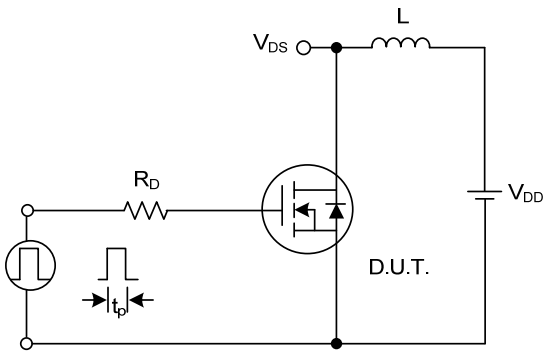
Switching Waveforms



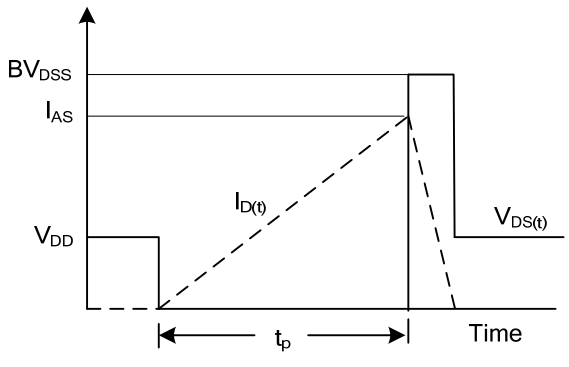
Gate Charge Test Circuit



Gate Charge Waveform



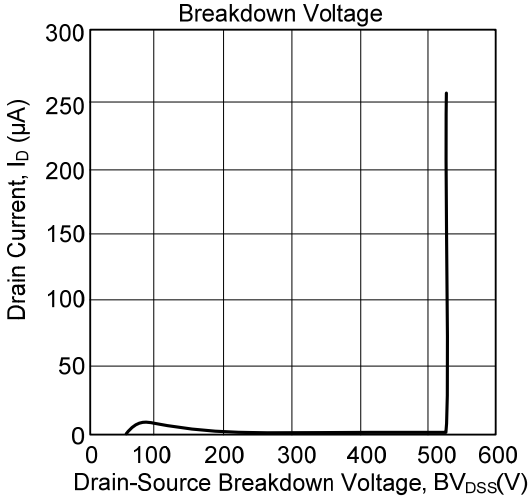
Unclamped Inductive Switching Test Circuit



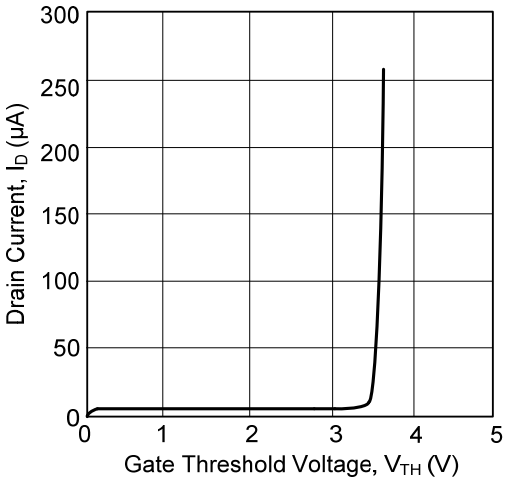
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

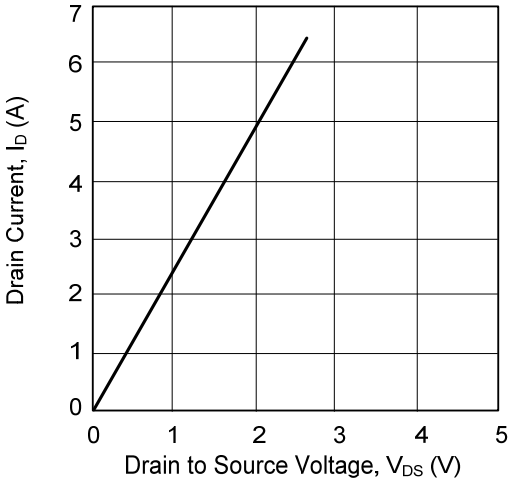
Drain Current vs. Drain-Source Breakdown Voltage



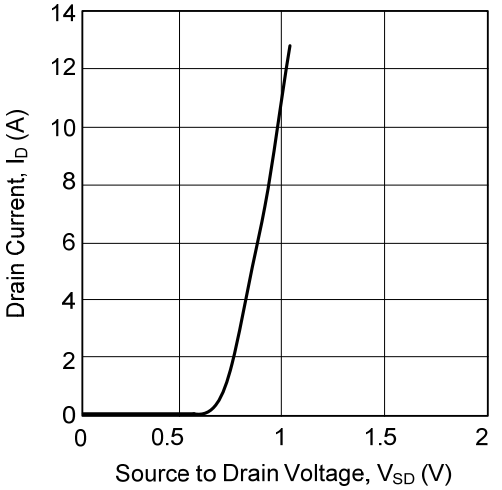
Drain Current vs. Gate Threshold Voltage



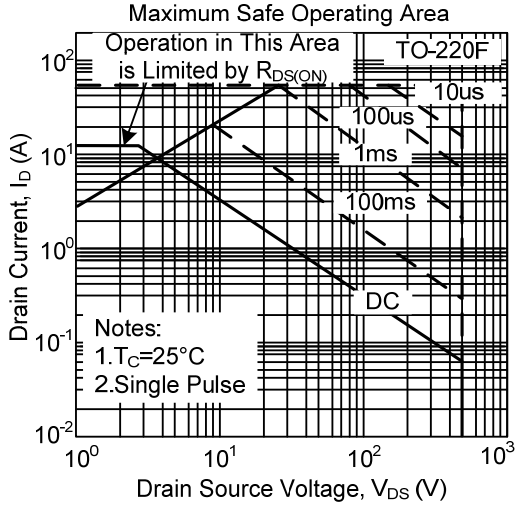
Drain-Source On-State Resistance Characteristics



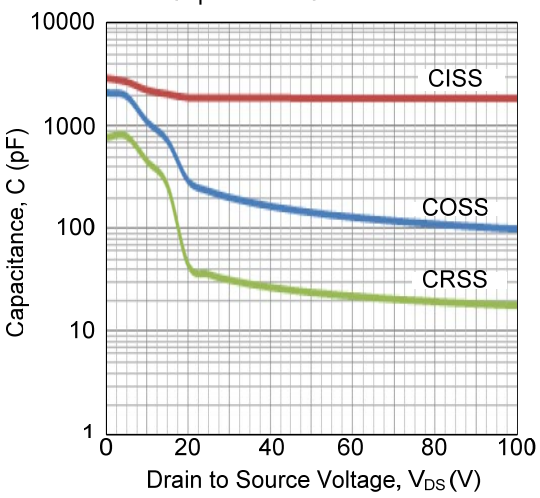
Drain Current vs. Source to Drain Voltage



Maximum Safe Operating Area



Capacitance Characteristics



■ TYPICAL CHARACTERISTICS